

SEMICONDUCTOR TECHNICAL DATA

2N5401S

EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE APPLICATION. HIGH VOLTAGE APPLICATION.

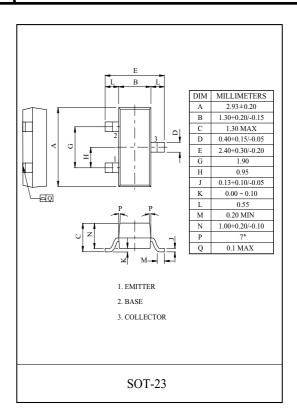
FEATURES

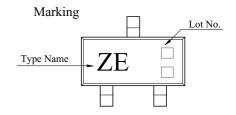
- · High Collector Breakdwon Voltage
 - $: V_{CBO} = -160V, V_{CEO} = -150V$
- · Low Leakage Current.
 - : I_{CBO} =-50nA(Max.) @ V_{CB} =-120V
- · Low Saturation Voltage
 - : $V_{CE(sat)}$ =-0.5V(Max.) @ I_{C} =-50mA, I_{B} =-5mA
- · Low Noise: NF=8dB (Max.)

MAXIMUM RATING (Ta=25)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Base Voltage	V _{CBO}	-160	V	
Collector-Emitter Voltage	V _{CEO}	-150	V	
Emitter-Base Voltage	V_{EBO}	-5	V	
Collector Current	I_{C}	-600	mA	
Base Current	I_{B}	-100	mA	
Collector Power Dissipation	P _C *	350	mW	
Junction Temperature	Tj	150		
Storage Temperature Range	T_{stg}	-55 150		

Note : * Package Mounted On 99.5% Alumina $10 \times 8 \times 0.6$ mm)





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ELECTRICAL CHARACTERISTICS (Ta=25)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} =-120V, I_{E} =0	-	-	-50	nA
		V_{CB} =-120V, I_{E} =0, Ta =100	-	-	-50	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} =-3V, I_{C} =0	-	-	-50	nA
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I_{C} =-0.1mA, I_{E} =0	-160	-	-	V
Collector-Emitter * Breakdown Voltage	V _{(BR)CEO}	I_{C} =-1mA, I_{B} =0	-150	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I_E =-10 μ A, I_C =0	-5	-	-	V
DC Current Gain *	h _{FE} (1)	V_{CE} =-5V, I_{C} =-1mA	50	-	-	
	h _{FE} (2)	V_{CE} =-5V, I_{C} =-10mA	60	-	240	
	h _{FE} (3)	V_{CE} =-5V, I_{C} =-50mA	50	-	-	
Collector-Emitter * Saturation Voltage	V _{CE(sat)} 1	I _C =-10mA, I _B =-1mA	-	-	-0.2	V
	V _{CE(sat)} 2	I_C =-50mA, I_B =-5mA	-	-	-0.5	
Base-Emitter *	V _{BE(sat)} 1	I _C =-10mA, I _B =-1mA	-	-	-1.0	V
Saturation Voltage	V _{BE(sat)} 2	I_C =-50mA, I_B =-5mA	-	-	-1.0	
Transition Frequency	f_T	V _{CE} =-10V, I _C =-10mA, f=100MHz	100	-	300	MHz
Collector Output Capacitance	C _{ob}	V_{CB} =-10V, I_E =0, f=1MHz	-	-	6	pF
Small-Signal Current Gain	h _{fe}	V_{CE} =-10V, I_{C} =-1mA, f =1kHz	40	-	200	
Noise Figure	NF	V_{CE} =-5V, I_{C} =-250 μ A Rg=1k , f=10Hz 15.7kHz	-	-	8	dB

^{*} Pulse Test: Pulse Width 300 \(\mathbb{S} \), Duty Cycle 2%.